

AMENDMENTS TO THE SPECIFICATION

Please amend paragraph [0038] as follows:

[0038] Figure 3 illustrates an exemplary multiplexer 320 that uses a negative voltage VSSL in memory cells 300A and 300B to suppress the sub-threshold leakage in pass transistors 310 and 311, which are coupled to output line 313. Note that transistors 301-306 perform substantially the same functions as transistors 201-206, and therefore are not explained in detail. However, of importance, transistors 303 and 305, when conducting, transfer negative voltage VSSL. Thus, memory cells 300A and 300B when programmed to output a logic zero provide this negative voltage VSSL. Negative voltage VSSL can be provided by any device for generating a predetermined voltage, e.g., a charge pump 314.